

When a first and second layer is applied to the substrate, the rough structure is advantageously transferred into the second layer, and the fine structure is transferred into the first layer. The rough structure may, for instance, consist

Please amend the following paragraph starting on page 4 at line 15, as follows:

Furthermore, in the case of the presence of a first and second layer on the substrate, it is advantageous when, in process step C), a etching agent which is selective for the second layer is used, and if applicable, an etching agent which is selective for the first layer is used in process step D). In this manner, it is possible to guarantee that only the respectively desired layers are structured in process steps C) and D). The selection of the etching agents in these processes depends on the consistency of the first and second layers. If the first layer is a metal layer and the second layer is a dielectric layer, such as $\text{SiO}_2/\text{SiO}_2$, it is possible, for instance, to use an HF process in C) and a sputter process in D).

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Please amend the following paragraph starting on page 5 at line ⁹~~20~~, as follows:

In process step B) of the procedure as it is embodied in the invention, a photoresist layer is advantageously produced, and structured into a mask structure using photo-lithography (structuring by means of exposure and subsequent development). Structured photoresist layers are particularly suitable as mask structures in the process as per the invention. It is, however, also possible to generate mask structures in process step B) which cannot be photo structured. For example, it would be possible to generate a polymer layer on the second layer, for instance a polyamide polyimide layer, and then structure this layer into a mask structure by means of structured etching ~~a structure through~~ a mask.

endowed with various elements, such as ~~aluminium~~ aluminum or indium, which are not identified individually here. On the p-endowed gallium nitride layer, which frequently shows poor electrical conductivity, contacts are mounted. These can, for instance, be produced using the process as per the invention. Namely, the bond pad 25 with the – for instance - additionally present recessed areas 25A which result from production by means of the process as per the invention, as well as a contact grate 30 for better transmission of the electrical current onto the pre-endowed gallium nitride layer 36. Furthermore, there is also an n-electrode present on the n-endowed gallium nitride layer. The contacts as per the invention can herein also be mounted on the n-endowed gallium nitride layer.

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Please amend the following paragraph starting on page ¹⁶~~14~~ at line ³~~10~~, as follows:
the mask structure is formed. This is then dried for 30 minutes at 120 ° C. In process step C), the second layer, the gold layer, is then etched with an aqueous cyanide containing ~~corrosive~~ etching medium for gold, wherein follow-up etching takes place for 1 ½ minutes in order to obtain good undercutting of the mask structure. The ~~corrosive~~ etching medium is then removed by flushing with water, and drying takes place in the spin rinse dryer at a maximum of 2400 revolutions per minute, wherein the undercut areas of the mask structure are additionally lowered onto the first layer, the platinum layer. Herein, additional drying takes place subsequently at low revolutions in the spin rinse dryer with nitrogen flow. After this process, the platinum layer is etched for 6 minutes in argon plasma, using sputter etching (process step D)). Then the mask structure is removed in a post-strip process.

Please replace the header on page 17, at line 3 with the following header:

~~Patent Claims~~ What is claimed is:

Please replace the header beginning at page 23, line 3, as follows:

~~Summary~~ Abstract